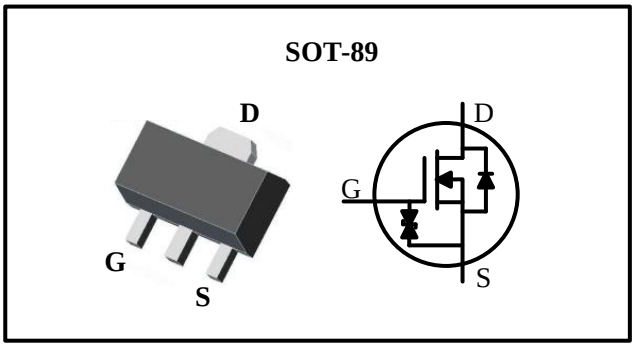
600V N-Channel Depletion-Mode Power MOSFET

General Features

- Depletion Mode (Normally-on)
- Free from Secondary Breakdown
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- ESD Improved Capability
- High Input Impedance
- RoHS Compliant
- Halogen-free Available

BV_{DSX}	$R_{DS(ON)(Typ.)}$	$I_{DSS(Min.)}$
600V	600 Ω	10mA



Applications

- Normally On Switches
- Constant Current Source
- Input Protection Circuits
- Power Supply Circuits
- Solid State Relays
- Converters

Ordering Information

Part Number	Package	Marking	Remark
DMX11C55EA	SOT-89	11C55	Halogen Free

Absolute Maximum Ratings

T_A=25℃ unless otherwise specified

Symbol	Parameter	DMX11C55EA	Unit
V_{DSX}	Drain-to-Source Voltage [1]	600	V
V_{DGX}	Drain-to-Gate Voltage [1]	600	V
I_D	Continuous Drain Current	0.028	A
I_{DM}	Pulsed Drain Current [2]	0.1	
P_D	Power Dissipation	1.0	W
V_{GS}	Gate-to-Source Voltage	±20	V
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	℃
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 150	℃

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMX11C55EA	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	125	℃/W

Electrical Characteristics

OFF Characteristics

T_A =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	600	--	--	V	V_{GS}=-5V, I_D=250μA
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	1	μA	V_{DS}=600V, V_{GS}=-5V
I_{GSS}	Gate-to-Source Leakage Current	--	--	10	μA	V_{GS}=20V, V_{DS}=0V
		--	--	-10		V_{GS}=-20V, V_{DS}=0V

ON Characteristics

T_A =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	10	--	30	mA	V_{GS}=0V, V_{DS}=25V
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	600	700	Ω	V_{GS}=0V, I_D=5mA [3]
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-3.3	--	-1.5	V	V_{DS}=3V, I_D=8μA
gfs	Forward Transconductance	--	14	--	mS	V_{DS}=10V, I_D=5mA

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	11.4	--	pF	V_{GS}=-5V V_{DS}=25V f=1.0MHz
C_{oss}	Output Capacitance	--	7.7	--		
C_{rss}	Reverse Transfer Capacitance	--	3.5	--		
Q_g	Total Gate Charge	--	0.56	--	nC	V_{GS}=-5V~5V V_{DS}=25V I_D=10mA
Q_{gs}	Gate-to-Source Charge	--	0.27	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	0.07	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(on)}$	Turn-on Delay Time	--	9.2	--	ns	V_{GS}=-5V~5V V_{DD}=25V I_D=10mA R_G=10 Ω
t_{rise}	Rise Time	--	30.0	--		
$t_{d(off)}$	Turn-off Delay Time	--	13.6	--		
t_{fall}	Fall Time	--	91.6	--		

Source-Drain Diode Characteristics

T_A=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.2	V	I_{SD}=5mA, V_{GS}=-5V

NOTE：

[1] T_J=+25℃ to +150℃.
[2] Repetitive rating, pulse width limited by maximum junction temperature.
[3] Pulse width≤380μs, duty cycle≤2%.

Typical Characteristics

Figure 1. Maximum Power Dissipation vs. Case Temperature

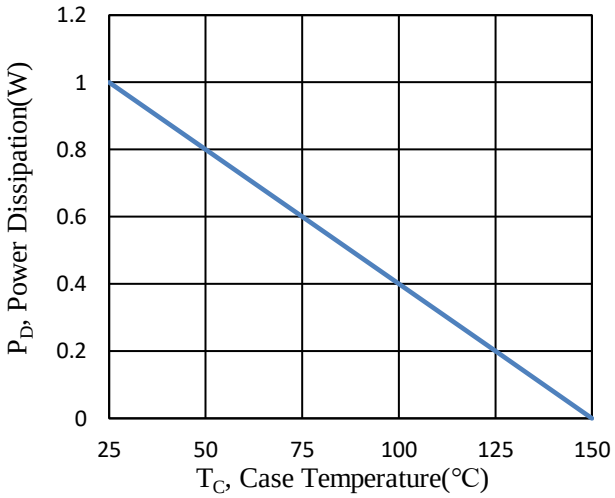


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

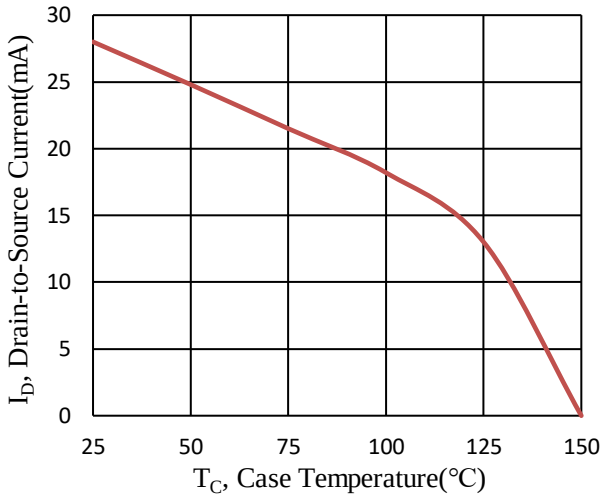


Figure 3. Typical Output Characteristics

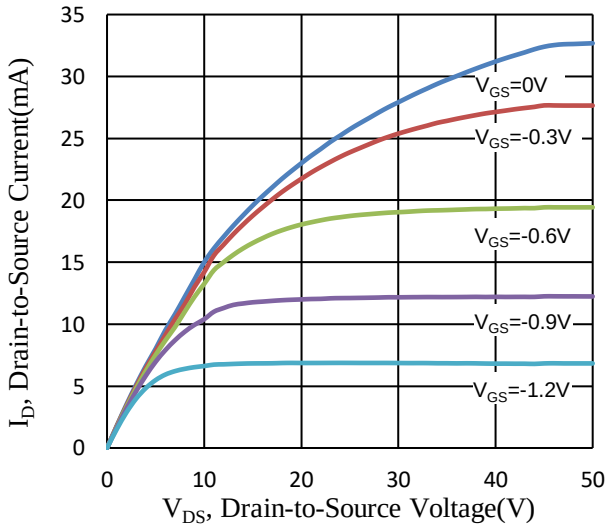


Figure 4. Typical Transfer Characteristics

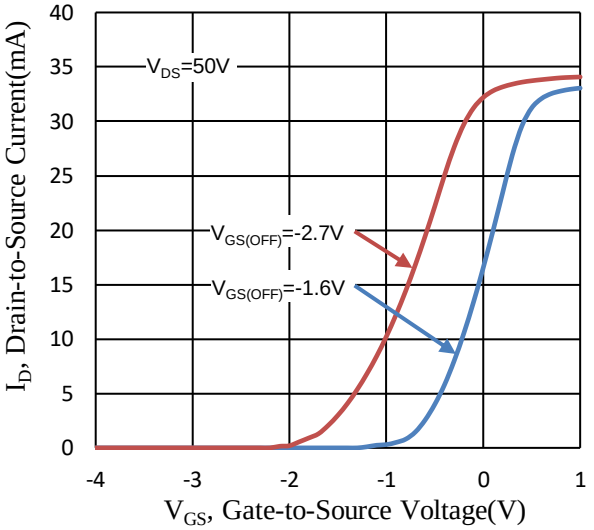


Figure 5. Typical Transfer Characteristics

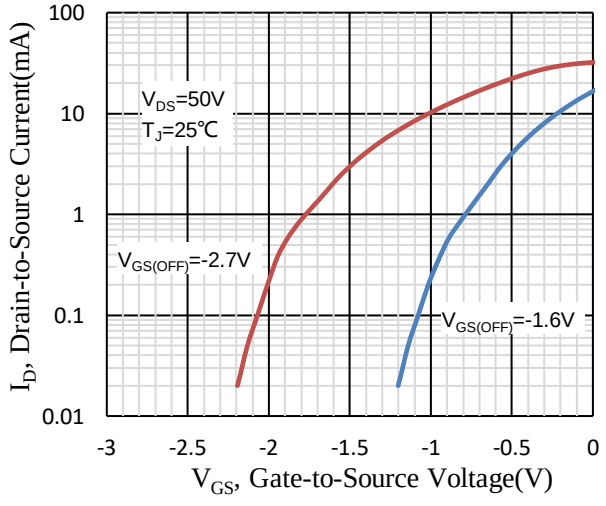


Figure 6. Typical Capacitance vs. Drain-to-Source Voltage

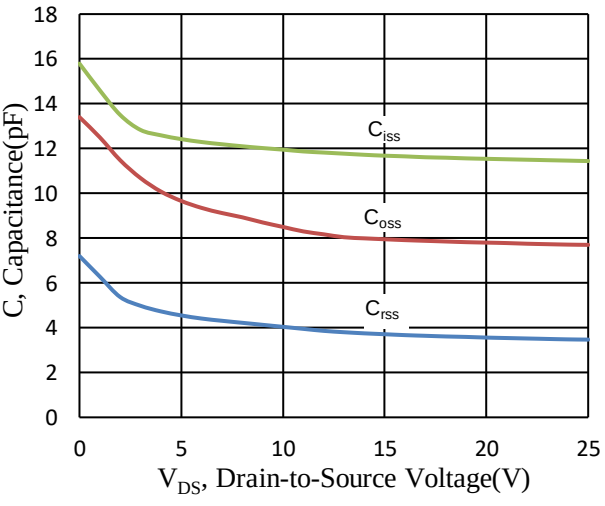


Figure 7. Typical Gate Charge vs. Gate-to-Source Voltage

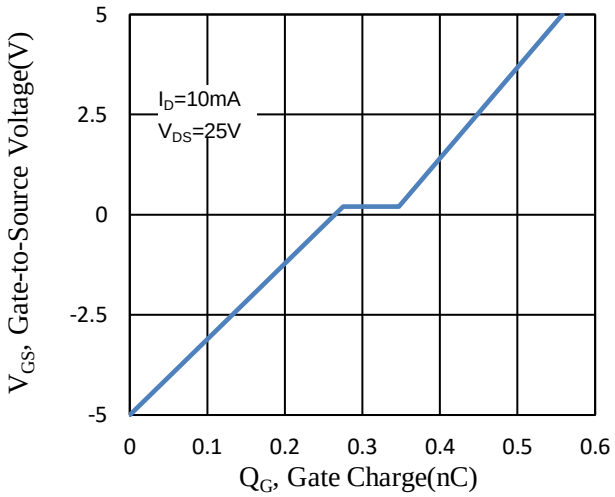


Figure 8. Normalized On-Resistance vs. Junction Temperature

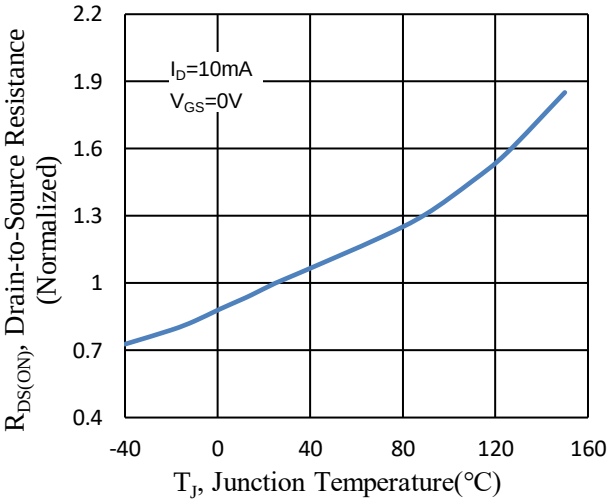


Figure 9. Gate-to-Source Cut-off Voltage vs. Junction Temperature

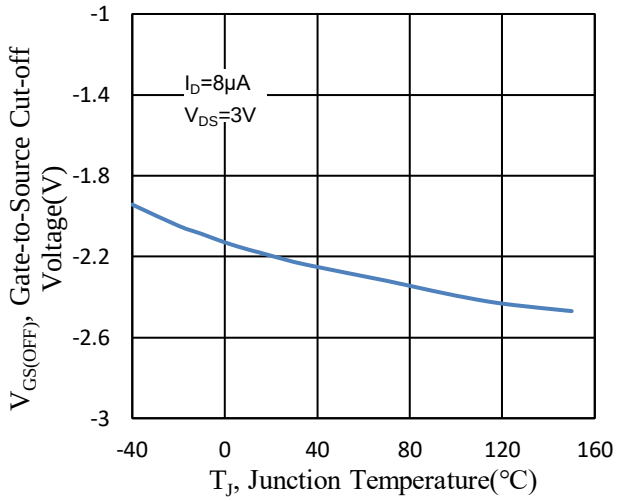


Figure 10. Drain-to-Source Breakdown Voltage vs. Junction Temperature

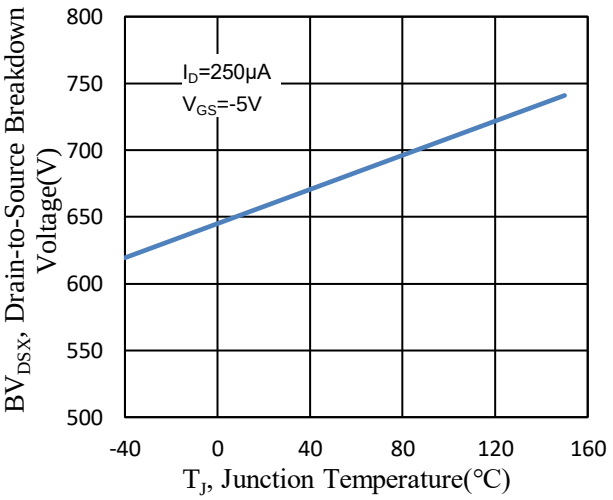
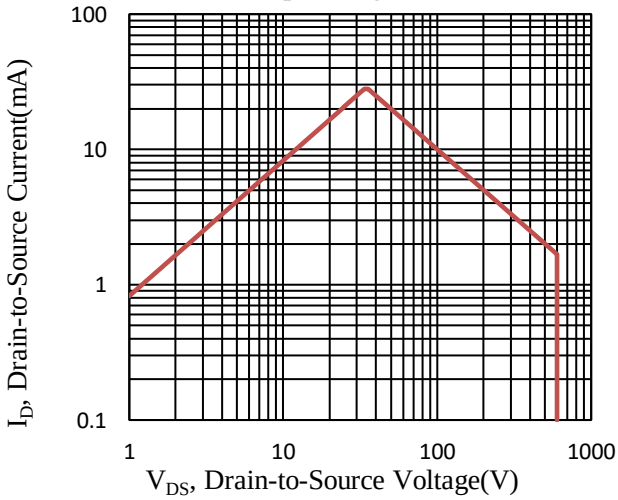
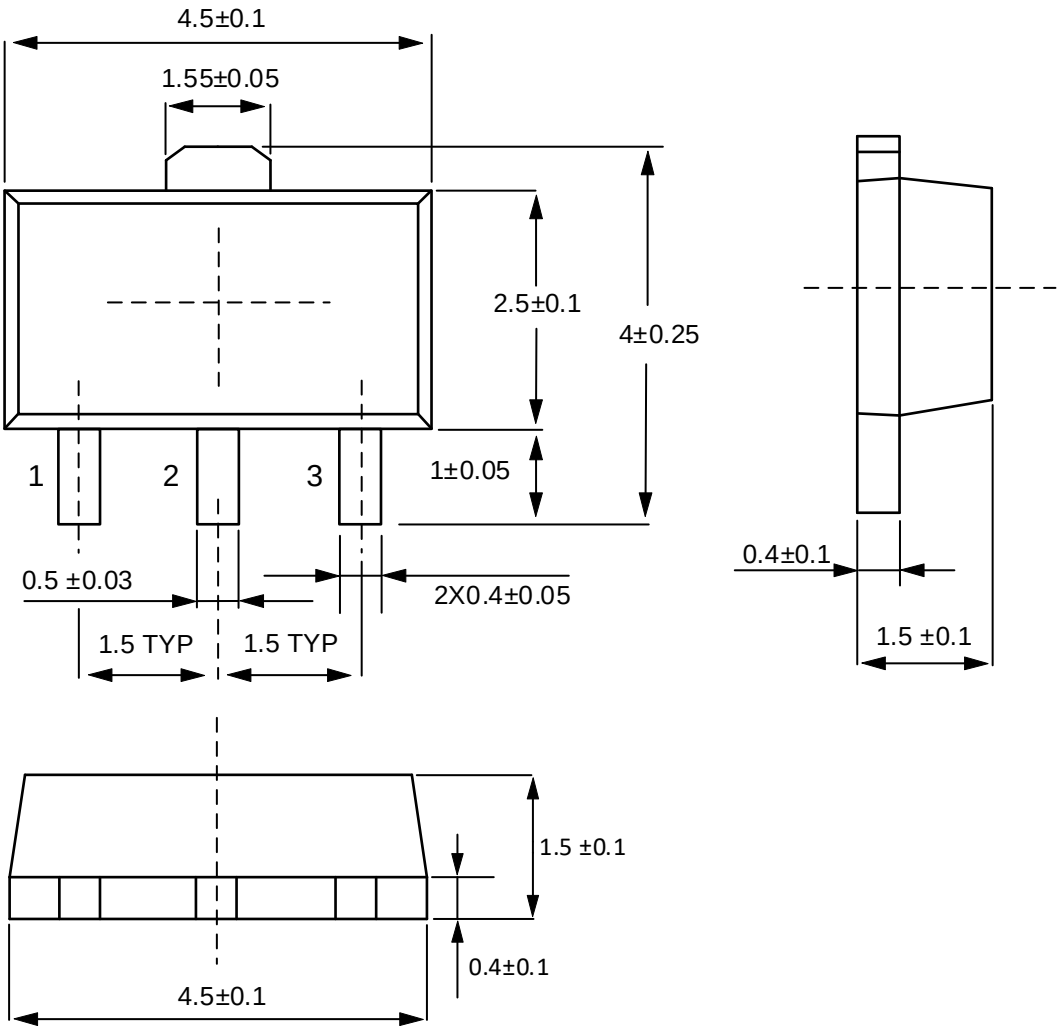


Figure 11. Maximum Forward Safe Operating Area



Package Dimensions

SOT-89



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